

N-Channel Power MOSFET

60V, 107A, 4.8mΩ

FEATURES

- Low R_{DS(ON)} to minimize conductive losses
- Logic level
- Low gate charge for fast power switching
- 100% UIS and R_g tested.
- 175°C Operating Junction Temperature
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

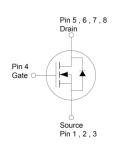
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- BLDC Motor Control
- Battery Power Management
- DC-DC converter
- Secondary Synchronous Rectification

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V_{DS}		60	V	
R _{DS(on)} (max)	$V_{GS} = 10V$	4.8	0	
	$V_{GS} = 4.5V$	6.8	mΩ	
Q_g		52	nC	







Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		107		
	$T_C = 25^{\circ}C$ $T_A = 25^{\circ}C$	l _D	16	A	
Pulsed Drain Current		I _{DM}	428	Α	
Single Pulse Avalanche Current (Note 2)		I _{AS}	35	Α	
Single Pulse Avalanche Energy (Note 2)		E _{AS}	184	mJ	
Total Davier Dissipation	$T_C = 25^{\circ}C$	Б	136	10/	
Total Power Dissipation	T _C = 125°C	P _D	45	W	
Total Power Dissipation	$T_A = 25$ °C	3.1		١٨/	
	$T_A = 125^{\circ}C$	P _D	1	W	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +175	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Case Thermal Resistance	R _{eJC}	1.1	°C/W		
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	48	°C/W		

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. The $R_{\Theta JA}$ limit presented here is based on mounting on a 1 in² pad of 2 oz copper.

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PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static		ı		1		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	60			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.8	2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
	$V_{GS} = 0V, V_{DS} = 60V$				1	
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 60V$ $T_{J} = 125^{\circ}C$	I _{DSS}			100	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 16A$	Б		4	4.8	mΩ
(Note 3)	$V_{GS} = 4.5V, I_D = 14A$	- R _{DS(on)}		4.8	6.8	
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 16A$	g _{fs}		66		S
Dynamic (Note 4)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 30V,$ $I_{D} = 16A$	Q_g		105		
Total Gate Charge		Qg		52		nC
Gate-Source Charge	$V_{GS} = 4.5V, V_{DS} = 30V,$	Q_{gs}		17		
Gate-Drain Charge	I _D = 14A	Q_{gd}		23		
Input Capacitance		C _{iss}		6253		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 30V$	C _{oss}		388		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		168		
Gate Resistance	f = 1.0MHz	R_g	0.5	1.8	3.6	Ω
Switching (Note 4)						
Turn-On Delay Time		t _{d(on)}		4		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 30V,$ $I_{D} = 16A, R_{G} = 2\Omega$	t _r		20		
Turn-Off Delay Time		t _{d(off)}		78		ns
Turn-Off Fall Time		t _f		38		
Source-Drain Diode						
Forward Voltage (Note 3)	V _{GS} = 0V, I _S = 16A	V_{SD}			1	V
Reverse Recovery Time	I _S = 16A ,	t _{rr}		25		ns
Reverse Recovery Charge	dl/dt = 100A/µs	Q _{rr}		18		nC

Notes:

- 1. Silicon limited current only.
- 2. L=0.3mH, $V_{GS}=10V$, $V_{DD}=30V$, $R_{G}=25\Omega$, $I_{AS}=35A$, Starting $T_{J}=25^{\circ}C$
- 3. Pulse test: Pulse Width \leq 300 μ s, duty cycle \leq 2%.
- 4. Switching time is essentially independent of operating temperature.

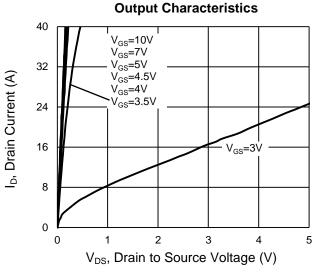
ORDERING INFORMATION

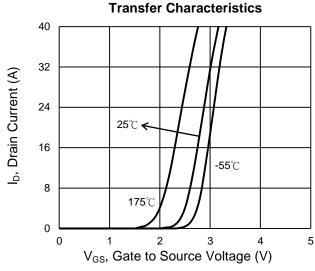
PART NO.	PACKAGE	PACKING
TSM048NB06LCR RLG	PDFN56	2,500pcs / 13" Reel

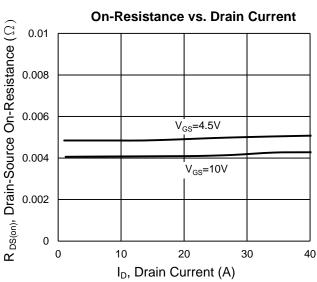


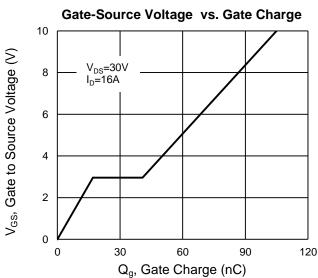
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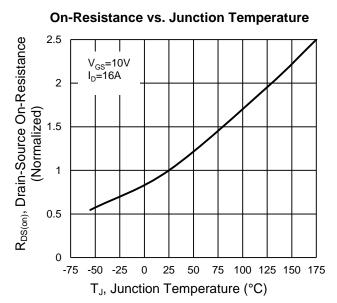
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

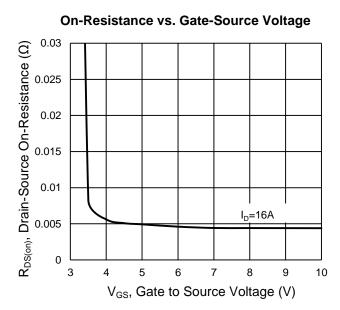










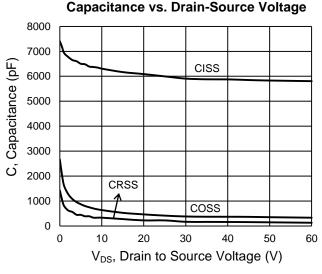


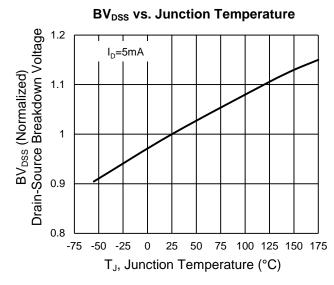
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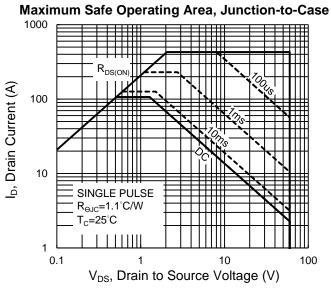


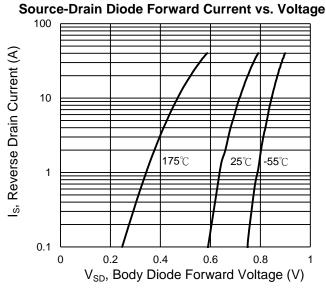
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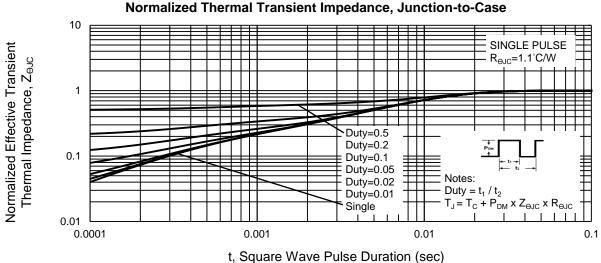
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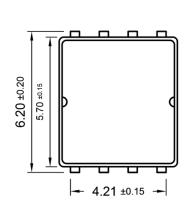


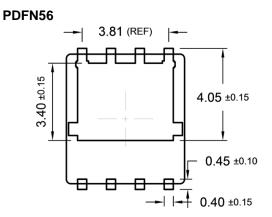
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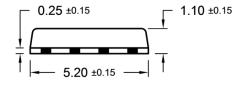


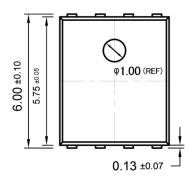
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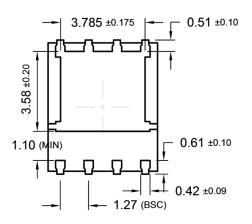
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

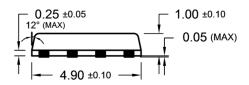




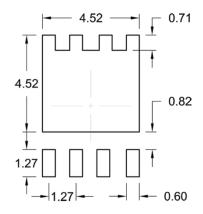




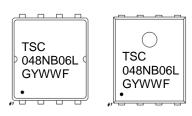




SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



G = Halogen Free

Y = Year Code

WW = Week Code (01~52)

F = Factory Code

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